

ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor device and an equipment for fabricating the semiconductor device are described.

According to the method and the equipment, a semiconductor substrate is irradiated with a particle beam through an opening formed in a thin film portion of a stencil mask having the thin film portion and a supporting portion supporting the thin film portion. The method and the equipment are controlled so that the supporting portion of the stencil mask can be irradiated with the fringe of the particle beam. As a result, the method and the equipment provide suppressing deterioration such as deformation or breakage of the stencil mask.